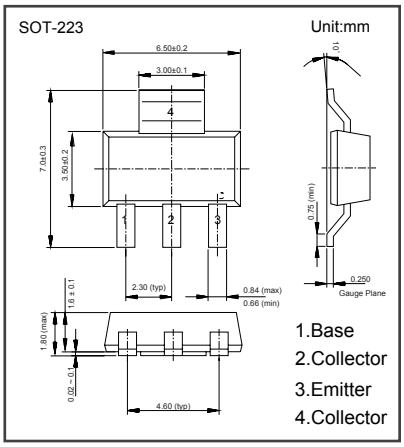
PNP Transistors

FZT790A (KZT790A)



■ Features

- Collector Current Capability I_C=-3A
- Collector Emitter Voltage V_{CEO}=-40V
- Complementary to FZT690B

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-50	V
Collector - Emitter Voltage	V_{CEO}	-40	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-3	A
Collector Current - Pluse	I_{CP}	-6	
Collector Power Dissipation	P_C	2	W
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -100 μA, I_E=0	-50			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -10 mA, I_B=0	-40			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 μ A, I_C=0	-5			
Collector-base cut-off current	I_{CBO}	V_{CB}= -30 V , I_E=0			-0.1	uA
		V_{CB}= -30 V , I_E=0 , Ta = 100℃			-10	
Emitter cut-off current	I_{EBO}	V_{EB}= -4V , I_C=0			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500 mA, I_B=-5mA			-0.25	V
		I_C=-1 A, I_B=-10mA			-0.45	
		I_C=-2 A, I_B=-50mA			-0.75	
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-1 A, I_B=-10mA			-1	
Base - emitter turn-on voltage	$V_{BE(on)}$	V_{CE}= -2V, I_C= -1 A		-0.75		
DC current gain	h_{FE}	V_{CE}= -2V, I_C= -10mA	300		800	
		V_{CE}= -2V, I_C= -500mA	250			
		VCE= -2V, IC= -1 A	200			
		V_{CE}= -2V, I_C= -2 A	150			
Switching Turn-on Times	t_{on}	I_C=-500mA, I_{B1}=-50mA, I_{B2}=-50mA, V_{CC}=-10V		35		ns
Switching Turn-off Times	t_{off}			600		
Collector output capacitance	C_{ob}	V_{CB}= -10V, f=1MHz		24		pF
Transition frequency	f_T	V_{CE}= -5V, I_C= -50mA,f=50MHz	100			MHz

Note.Pulse width=300us. Duty cycle ≤ 2%

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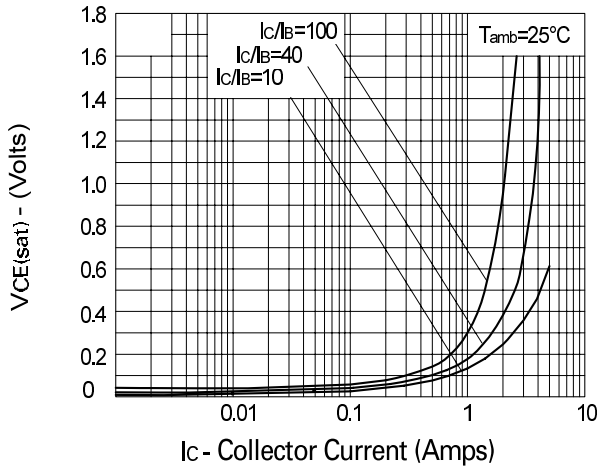
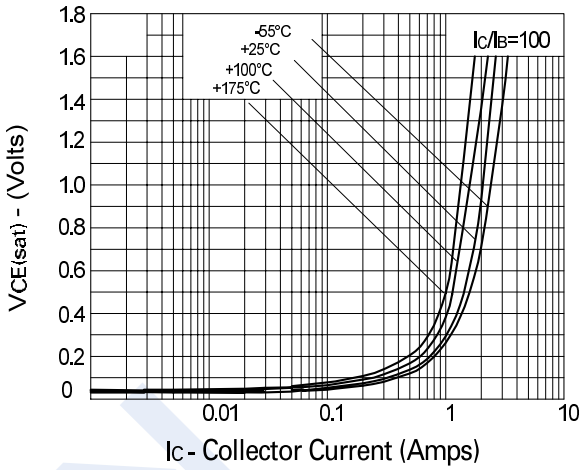
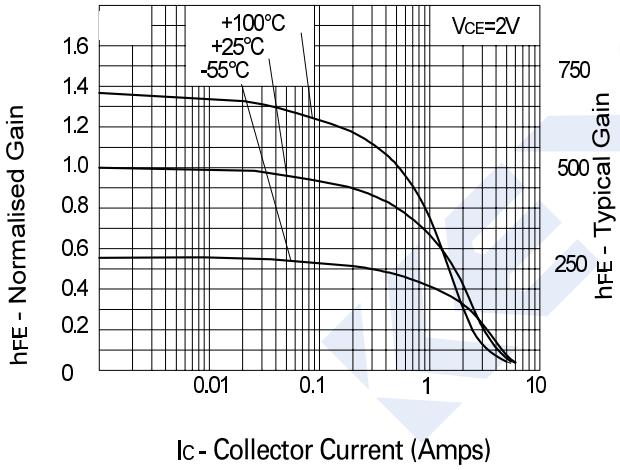
■ Typical Characterisitics



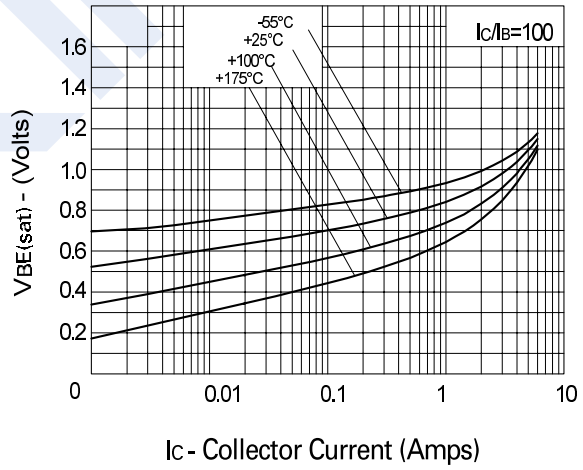
VCE(sat) v IC



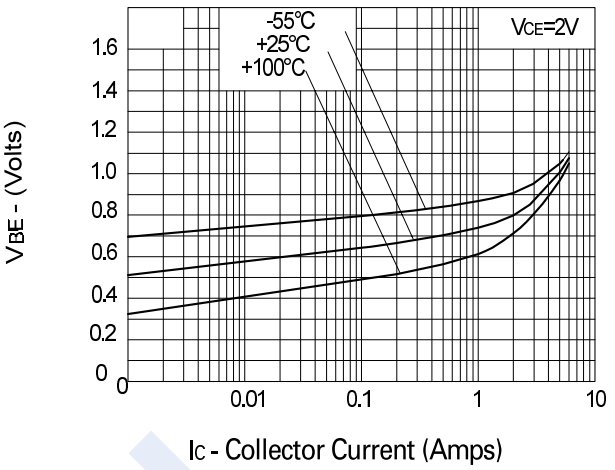
VCE(sat) v IC



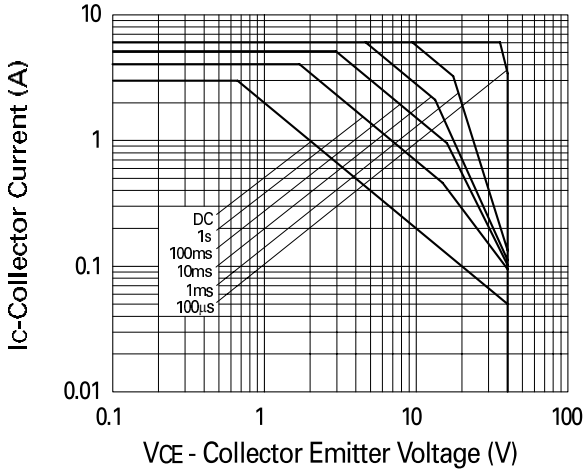
hFE v IC



VBE(sat) v IC



VBE(on) v IC



Safe Operating Area